



# PSMN8R9-100BSE

N-channel 100 V, 10 mOhm, standard level MOSFET in D2PAK

28 October 2020

Product data sheet

## 1. General description

SuperSOA N-channel enhancement mode MOSFET in a D2PAK package qualified to 175 °C. PSMN8R9-100BSE delivers low  $R_{DS(on)}$  and very strong linear-mode (SOA) performance, and complements the latest "hot-swap" controllers - robust enough to withstand substantial inrush currents during turn on, low  $R_{DS(on)}$  to minimize  $I^2R$  losses and deliver optimum efficiency when turned fully ON.

## 2. Features and benefits

- Avalanche rated, 100% tested
- Low  $R_{DS(on)}$  for low  $I^2R$  conduction losses
- D2PAK package

## 3. Applications

- Hot swap
- Load switch
- Soft start
- E-fuse
- Telecommunication systems based on a 48 V backplane/supply rail

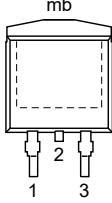
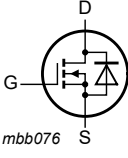
## 4. Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                                    | Conditions                                                                                                                                                       |  | Min | Typ | Max | Unit |
|-------------------------|----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|-----|-----|------|
| V <sub>DS</sub>         | drain-source voltage                         | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                                                                                                                  |  | -   | -   | 100 | V    |
| I <sub>D</sub>          | drain current                                | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>                                                                                          |  | -   | -   | 75  | A    |
| I <sub>DM</sub>         | peak drain current                           | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 3</a>                                                                                  |  | -   | -   | 419 | A    |
| P <sub>tot</sub>        | total power dissipation                      | T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>                                                                                                                  |  | -   | -   | 296 | W    |
| Static characteristics  |                                              |                                                                                                                                                                  |  |     |     |     |      |
| R <sub>DSon</sub>       | drain-source on-state resistance             | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>                                                                   |  | -   | 8   | 10  | mΩ   |
| Dynamic characteristics |                                              |                                                                                                                                                                  |  |     |     |     |      |
| Q <sub>GD</sub>         | gate-drain charge                            | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>                                         |  | -   | 32  | 45  | nC   |
| Q <sub>G(tot)</sub>     | total gate charge                            |                                                                                                                                                                  |  | -   | 114 | 160 | nC   |
| Avalanche ruggedness    |                                              |                                                                                                                                                                  |  |     |     |     |      |
| E <sub>DS(AL)S</sub>    | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 75 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; <a href="#">Fig. 4</a> |  | -   | -   | 422 | mJ   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                  | Graphic symbol                                                                                |
|-----|--------|-----------------------------------|-----------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | G      | gate                              | <br>D2PAK (SOT404) | <br>mbb076 |
| 2   | D      | drain[1]                          |                                                                                                     |                                                                                               |
| 3   | S      | source                            |                                                                                                     |                                                                                               |
| mb  | D      | mounting base; connected to drain |                                                                                                     |                                                                                               |

[1] It is not possible to make connection to pin 2.

## 6. Ordering information

Table 3. Ordering information

| Type number    | Package |                                                                                                                                   |         |
|----------------|---------|-----------------------------------------------------------------------------------------------------------------------------------|---------|
|                | Name    | Description                                                                                                                       | Version |
| PSMN8R9-100BSE | D2PAK   | plastic, single-ended surface-mounted package (D2PAK); 3 terminals (one lead cropped); 2.54 mm pitch; 11 mm x 10 mm x 4.3 mm body | SOT404  |

## 7. Marking

Table 4. Marking codes

| Type number    | Marking code      |
|----------------|-------------------|
| PSMN8R9-100BSE | PSMN8R9<br>100BSE |

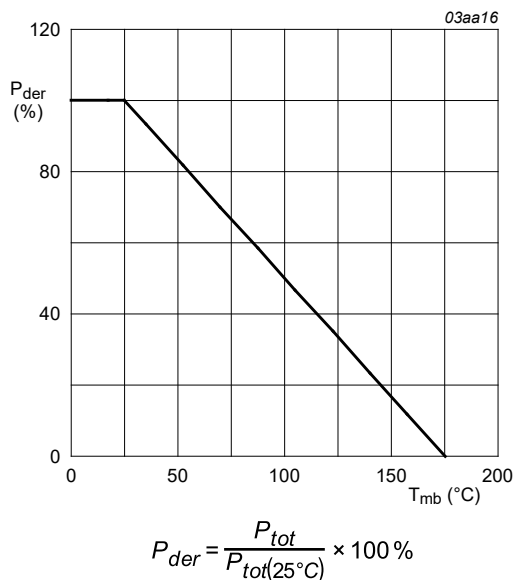
## 8. Limiting values

Table 5. Limiting values

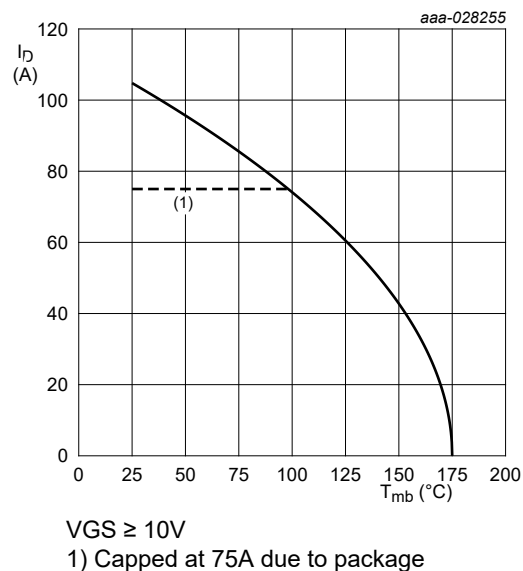
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter                  | Conditions                                                                                            | Min | Max | Unit               |
|---------------------------|----------------------------|-------------------------------------------------------------------------------------------------------|-----|-----|--------------------|
| $V_{DS}$                  | drain-source voltage       | $25\text{ }^{\circ}\text{C} \leq T_j \leq 175\text{ }^{\circ}\text{C}$                                | -   | 100 | V                  |
| $V_{DGR}$                 | drain-gate voltage         | $25\text{ }^{\circ}\text{C} \leq T_j \leq 175\text{ }^{\circ}\text{C}$ ; $R_{GS} = 20\text{ k}\Omega$ | -   | 100 | V                  |
| $V_{GS}$                  | gate-source voltage        |                                                                                                       | -20 | 20  | V                  |
| $P_{tot}$                 | total power dissipation    | $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 1                                                        | -   | 296 | W                  |
| $I_D$                     | drain current              | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 2                               | -   | 75  | A                  |
|                           |                            | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ }^{\circ}\text{C}$ ; Fig. 2                              | -   | 74  | A                  |
| $I_{DM}$                  | peak drain current         | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 3             | -   | 419 | A                  |
| $T_{stg}$                 | storage temperature        |                                                                                                       | -55 | 175 | $^{\circ}\text{C}$ |
| $T_j$                     | junction temperature       |                                                                                                       | -55 | 175 | $^{\circ}\text{C}$ |
| $T_{slid(M)}$             | peak soldering temperature |                                                                                                       | -   | 260 | $^{\circ}\text{C}$ |
| <b>Source-drain diode</b> |                            |                                                                                                       |     |     |                    |
| $I_S$                     | source current             | $T_{mb} = 25\text{ }^{\circ}\text{C}$                                                                 | -   | 75  | A                  |

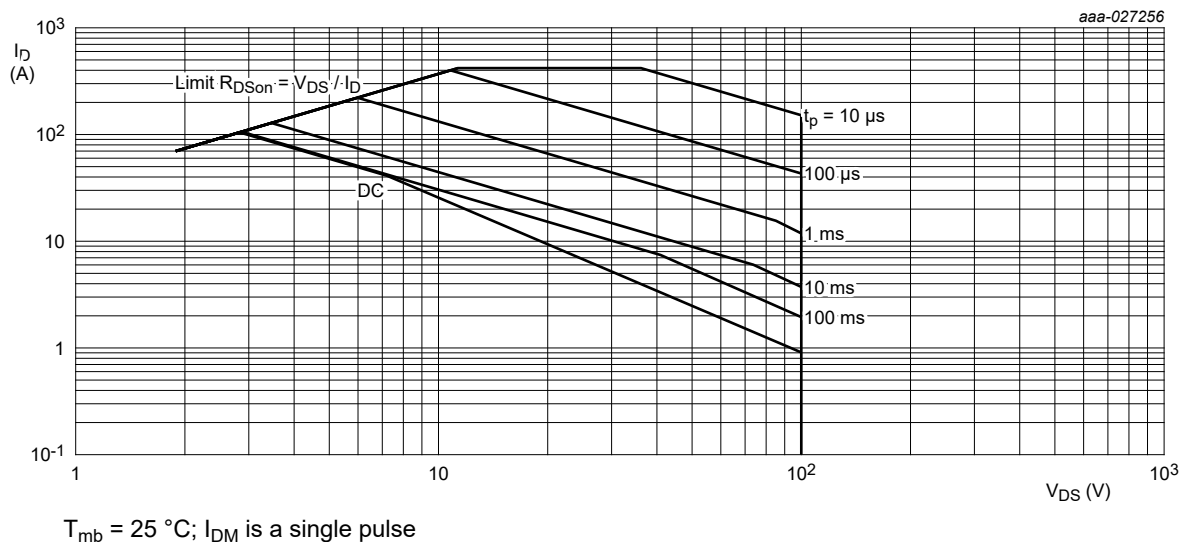
| Symbol                      | Parameter                                    | Conditions                                                                                                                                    | Min | Max | Unit |
|-----------------------------|----------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10 \mu s$ ; $T_{mb} = 25^\circ C$                                                                                           | -   | 419 | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                               |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 75 A$ ; $V_{sup} \leq 100 V$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 V$ ; $T_{j(init)} = 25^\circ C$ ; unclamped; <a href="#">Fig. 4</a> | -   | 422 | mJ   |



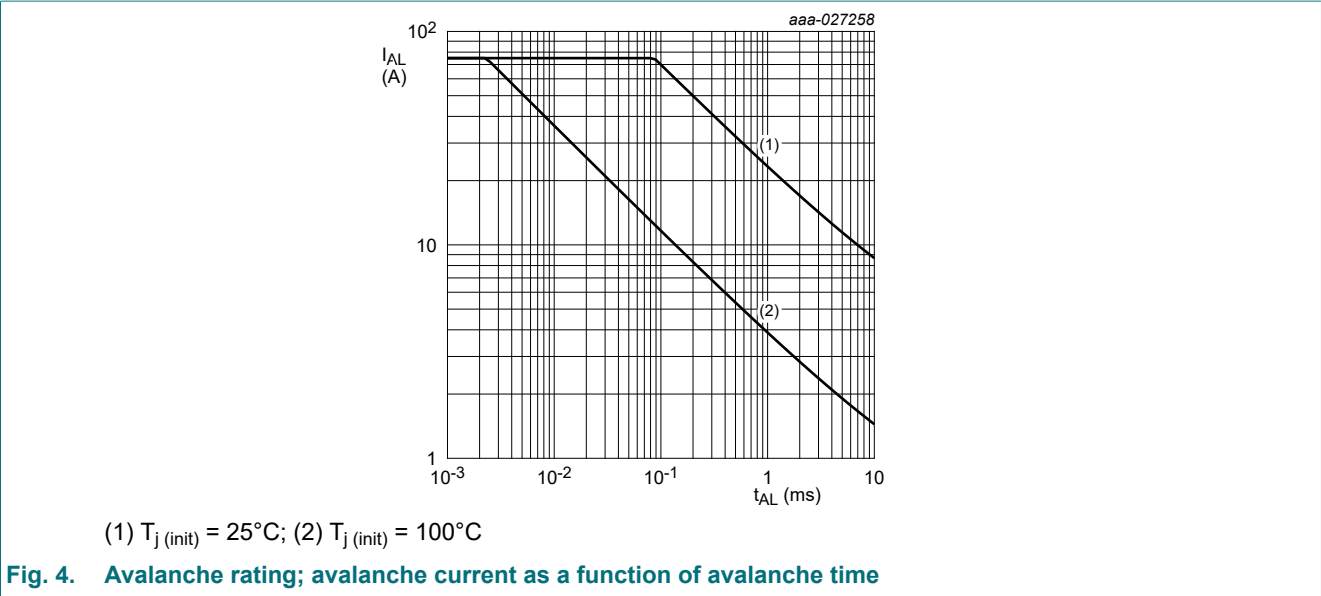
**Fig. 1.** Normalized total power dissipation as a function of mounting base temperature



**Fig. 2.** Continuous drain current as a function of mounting base temperature



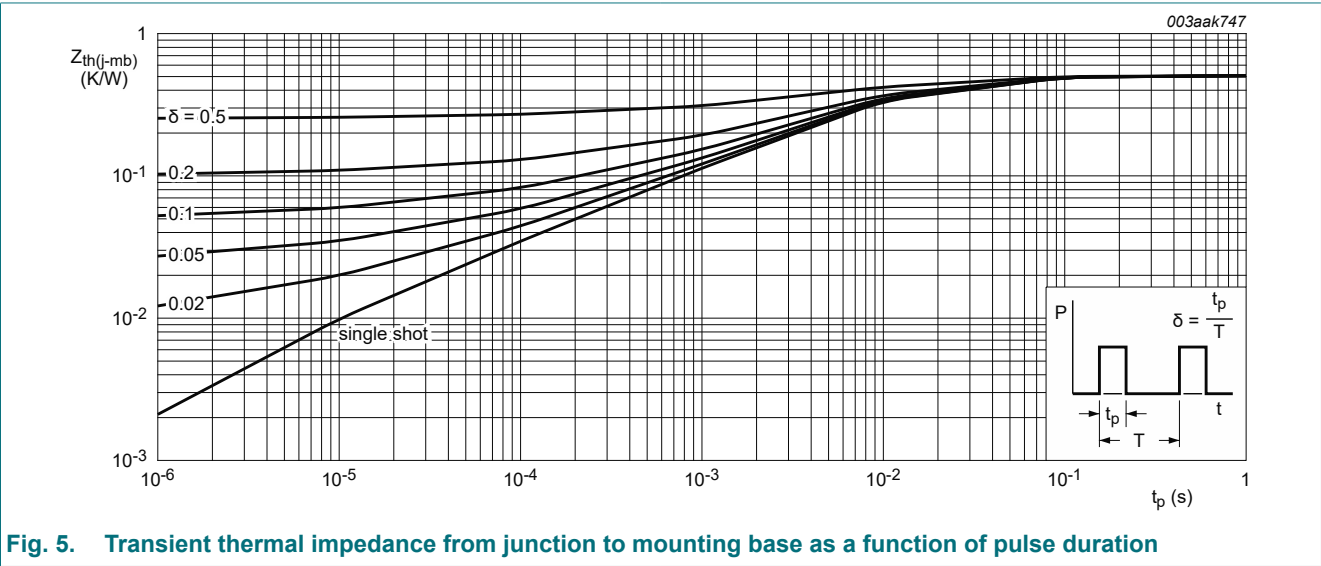
**Fig. 3.** Safe operating area; continuous and peak drain currents as a function of drain-source voltage



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions |  | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------|--|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5     |  | -   | 0.42 | 0.51 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       |            |  | -   | 50   | -    | K/W  |



## 10. Characteristics

Table 7. Characteristics

| Symbol                  | Parameter                         | Conditions                                                                                                                          |  | Min | Typ  | Max  | Unit |
|-------------------------|-----------------------------------|-------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| Static characteristics  |                                   |                                                                                                                                     |  |     |      |      |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage    | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                              |  | 100 | -    | -    | V    |
|                         |                                   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = -55 °C                                                             |  | 90  | -    | -    | V    |
| V <sub>GS(th)</sub>     | gate-source threshold voltage     | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = 25 °C; <a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a> |  | 1.8 | 2.7  | 4    | V    |
|                         |                                   | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = 175 °C; <a href="#">Fig. 11</a>                          |  | 1   | -    | -    | V    |
|                         |                                   | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = -55 °C; <a href="#">Fig. 11</a>                          |  | -   | -    | 4.6  | V    |
| I <sub>DSS</sub>        | drain leakage current             | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                              |  | -   | 0.1  | 2    | μA   |
|                         |                                   | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 175 °C                                                             |  | -   | -    | 500  | μA   |
| I <sub>GSS</sub>        | gate leakage current              | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                               |  | -   | 2    | 100  | nA   |
|                         |                                   | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                              |  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>       | drain-source on-state resistance  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 12</a>                                      |  | -   | 8    | 10   | mΩ   |
|                         |                                   | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 100 °C; <a href="#">Fig. 13</a>                                     |  | -   | -    | 18.5 | mΩ   |
|                         |                                   | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 175 °C; <a href="#">Fig. 13</a>                                     |  | -   | -    | 27   | mΩ   |
| R <sub>G</sub>          | gate resistance                   | f = 1 MHz                                                                                                                           |  | 0.4 | 0.8  | 1.6  | mΩ   |
| Dynamic characteristics |                                   |                                                                                                                                     |  |     |      |      |      |
| Q <sub>G(tot)</sub>     | total gate charge                 | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>            |  | -   | 114  | 160  | nC   |
|                         |                                   | I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V                                                                 |  | -   | 45   | 63   | nC   |
| Q <sub>GS</sub>         | gate-source charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>            |  | -   | 33   | 46   | nC   |
| Q <sub>GS(th)</sub>     | pre-threshold gate-source charge  |                                                                                                                                     |  | -   | 18   | -    | nC   |
| Q <sub>GS(th-pl)</sub>  | post-threshold gate-source charge |                                                                                                                                     |  | -   | 15   | -    | nC   |
| Q <sub>GD</sub>         | gate-drain charge                 |                                                                                                                                     |  | -   | 32   | 45   | nC   |
| V <sub>GS(pl)</sub>     | gate-source plateau voltage       | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>                                    |  | -   | 5.3  | -    | V    |
| C <sub>iss</sub>        | input capacitance                 | V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>J</sub> = 25 °C; <a href="#">Fig. 16</a>                           |  | -   | 7028 | 9488 | pF   |
| C <sub>oss</sub>        | output capacitance                |                                                                                                                                     |  | -   | 447  | 603  | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance      |                                                                                                                                     |  | -   | 237  | 332  | pF   |
| t <sub>d(on)</sub>      | turn-on delay time                | V <sub>DS</sub> = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω                                     |  | -   | 28   | 42   | ns   |
| t <sub>r</sub>          | rise time                         |                                                                                                                                     |  | -   | 52   | 78   | ns   |
| t <sub>d(off)</sub>     | turn-off delay time               |                                                                                                                                     |  | -   | 60   | 90   | ns   |
| t <sub>f</sub>          | fall time                         |                                                                                                                                     |  | -   | 44   | 66   | ns   |
| Source-drain diode      |                                   |                                                                                                                                     |  |     |      |      |      |
| V <sub>SD</sub>         | source-drain voltage              | I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 17</a>                                       |  | -   | 0.83 | 1.2  | V    |

| Symbol   | Parameter             | Conditions                                                                            |     | Min | Typ | Max | Unit |
|----------|-----------------------|---------------------------------------------------------------------------------------|-----|-----|-----|-----|------|
| $t_{rr}$ | reverse recovery time | $I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; |     | -   | 77  | 100 | ns   |
| $Q_r$    | recovered charge      | $V_{DS} = 50\text{ V}$                                                                | [1] | -   | 248 | 322 | nC   |

[1] includes capacitive recovery

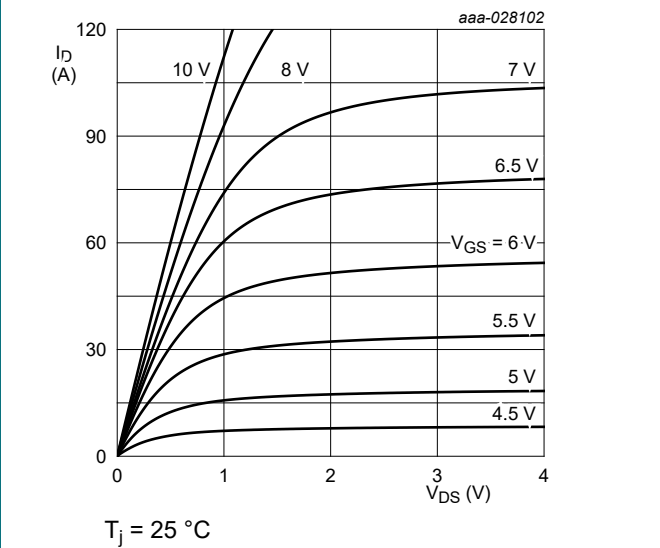


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

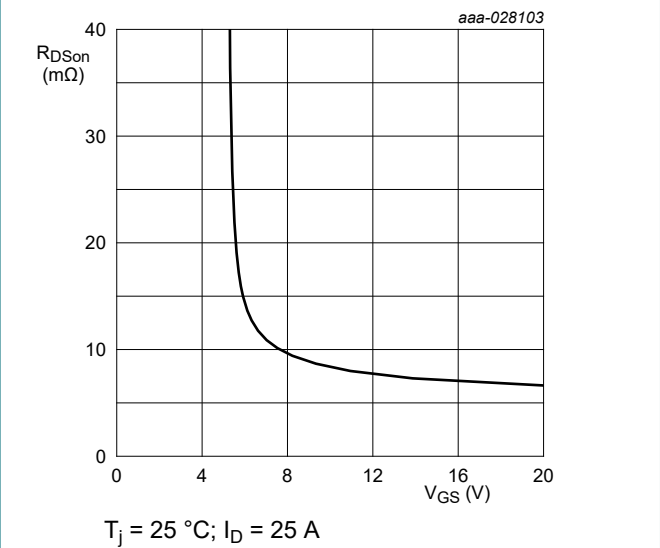


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

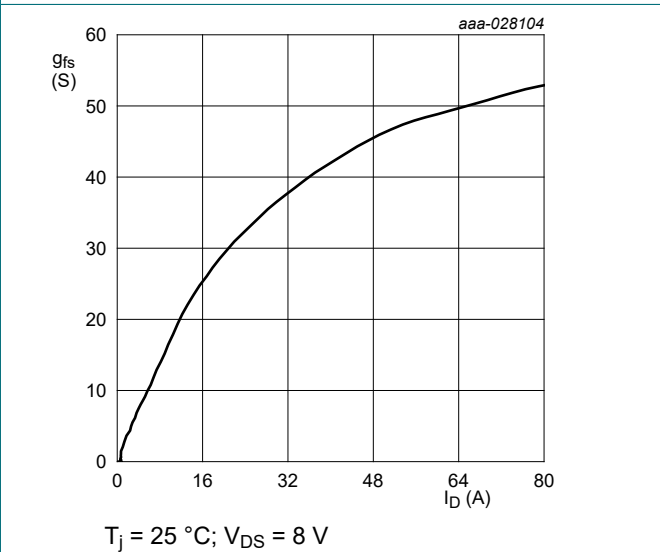


Fig. 8. Forward transconductance as a function of drain current; typical values

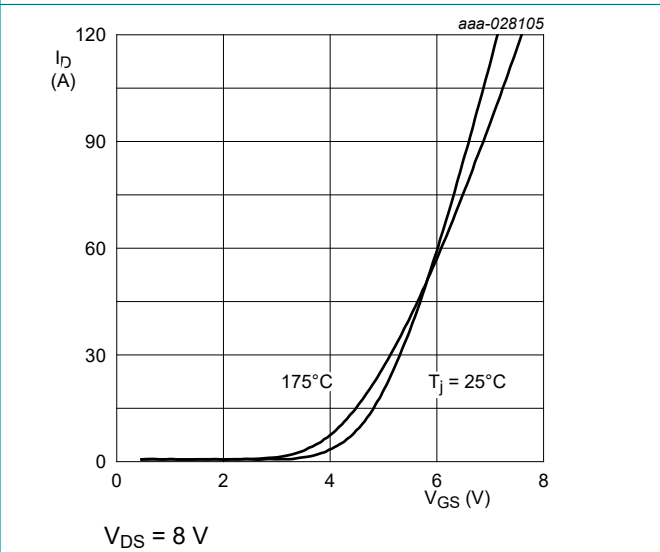


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

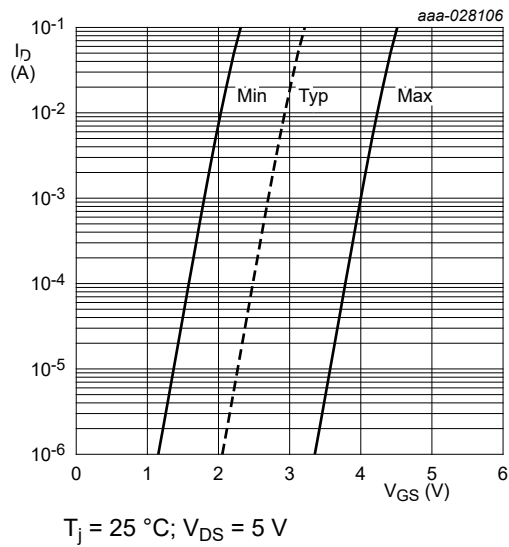


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

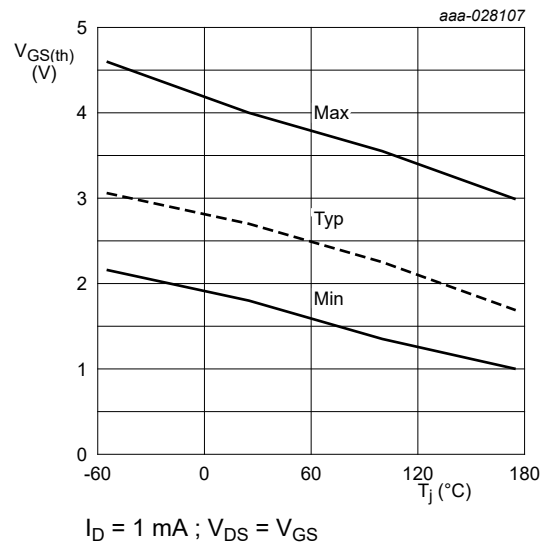


Fig. 11. Gate-source threshold voltage as a function of junction temperature

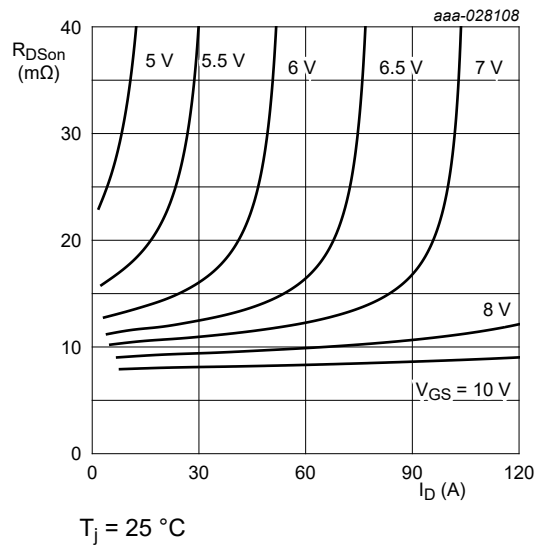


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

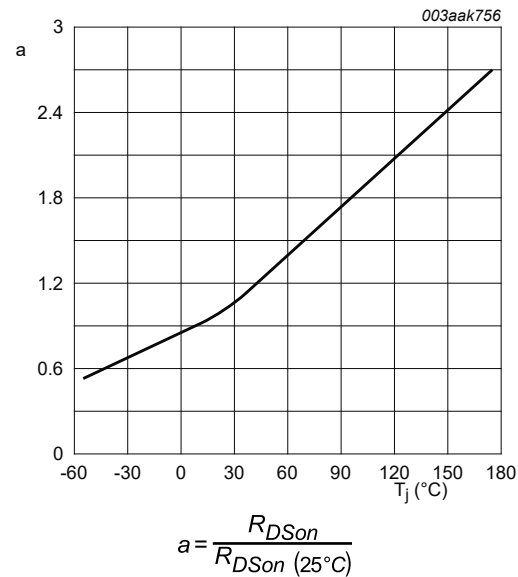


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

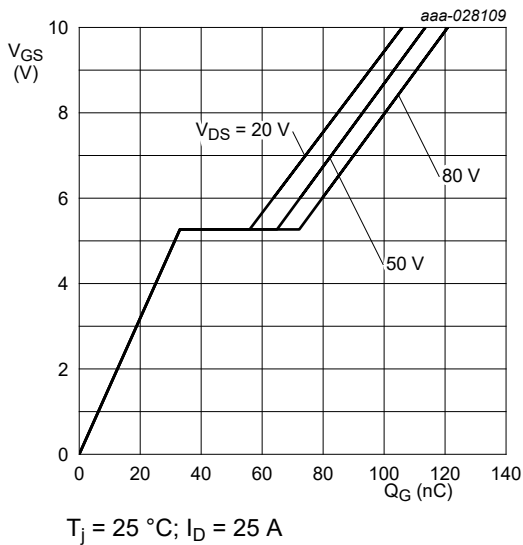


Fig. 14. Gate-source voltage as a function of gate charge; typical values

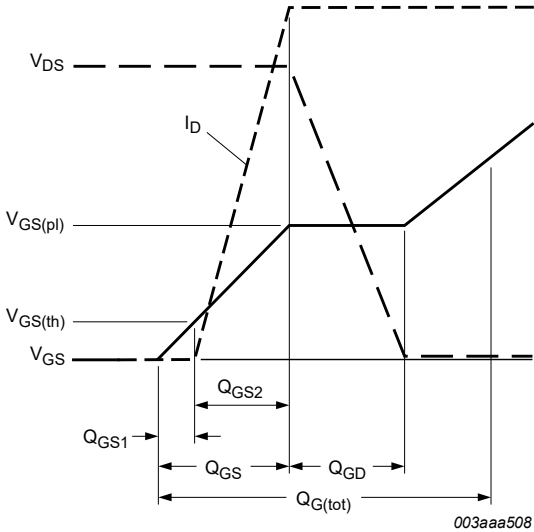


Fig. 15. Gate charge waveform definitions

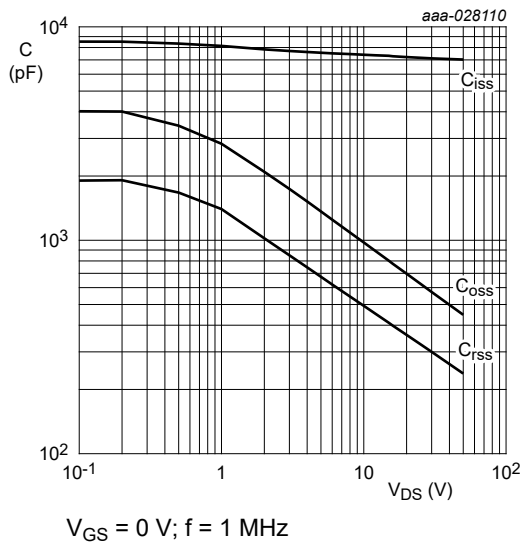


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

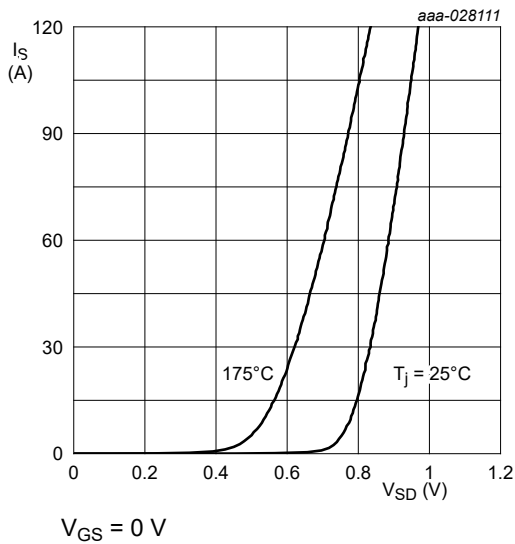


Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

11. Package outline

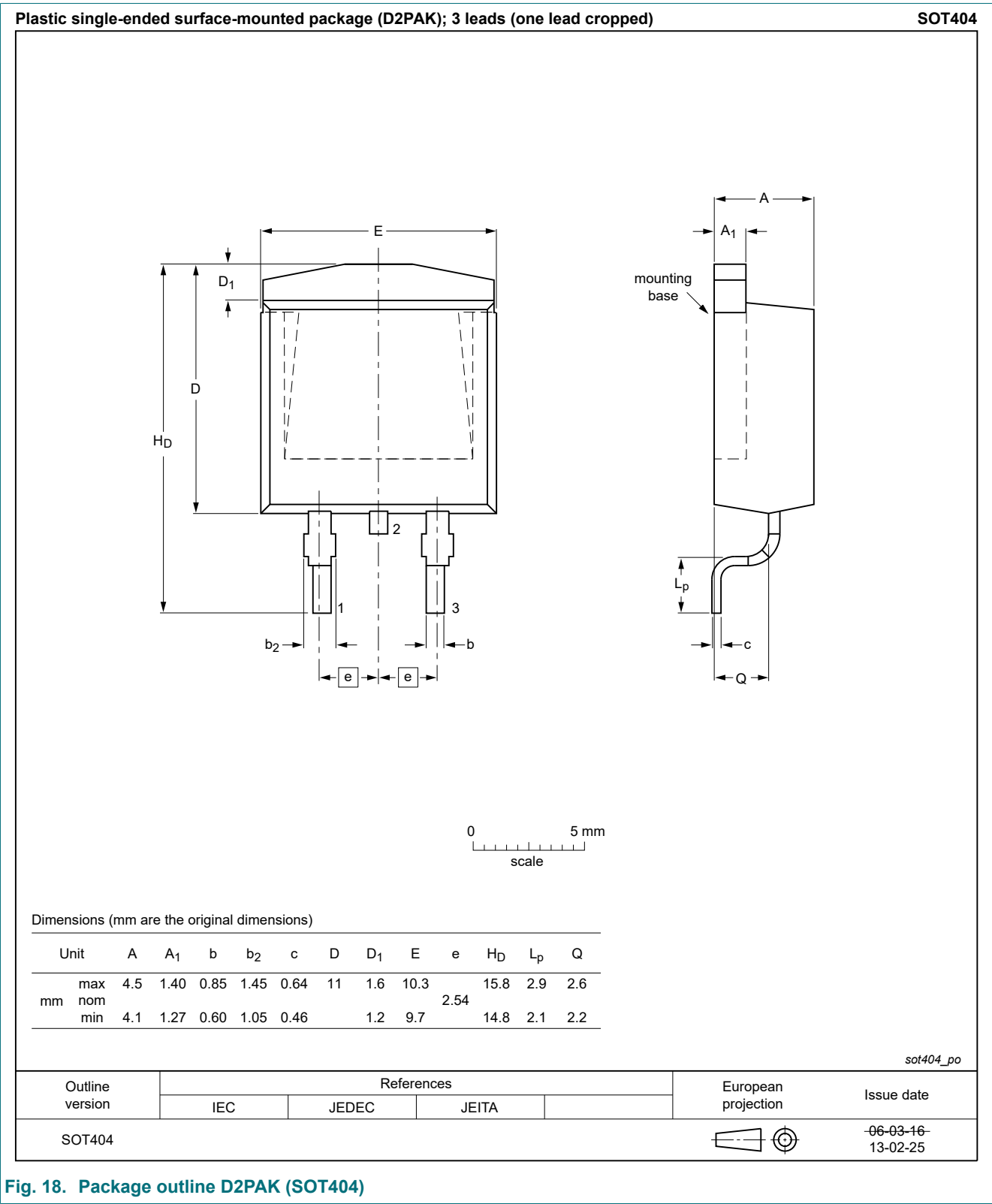


Fig. 18. Package outline D2PAK (SOT404)

12. Soldering

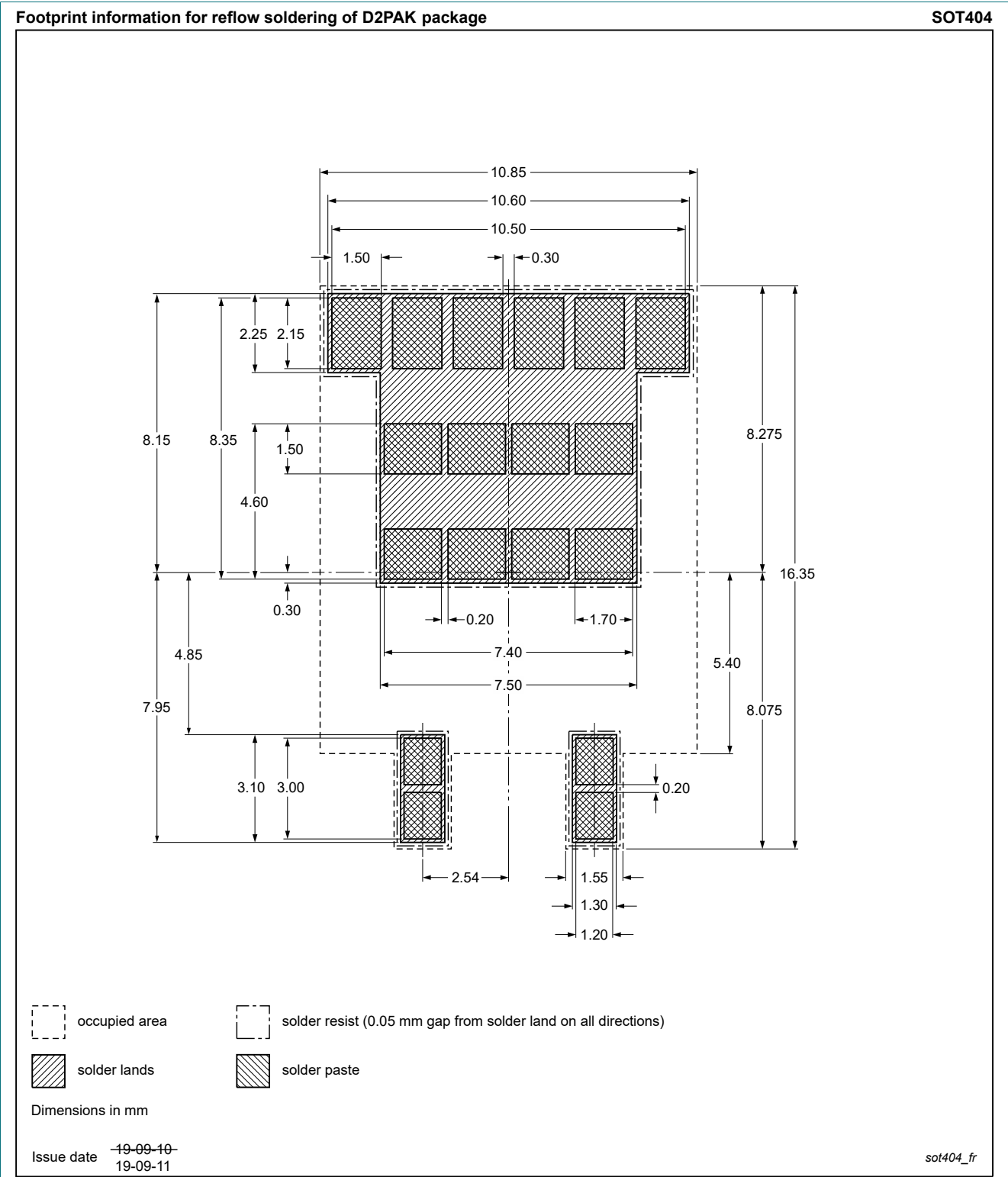


Fig. 19. Reflow soldering footprint for D2PAK (SOT404)

## 13. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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